

isc N-Channel MOSFET Transistor

IRFP064N

FEATURES

- Static drain-source on-resistance: $\mathsf{R} \mathsf{D} \mathsf{s}(\mathsf{on}) \! \leqslant \! 8 \mathsf{m} \Omega$
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

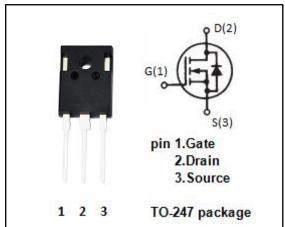
- Ultra Low On-resistance
- · Fast Switching

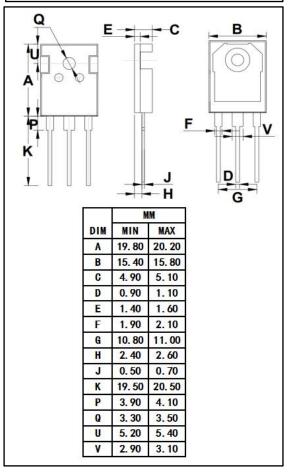
• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT	
V _{DSS}	Drain-Source Voltage	55	V	
V_{GS}	Gate-Source Voltage	±20	V	
I _D	Drain Current-Continuous	110	Α	
I _{DM}	Drain Current-Single Pulsed	390	Α	
P _D	Total Dissipation @T _C =25℃	200	W	
Tj	Max. Operating Junction Temperature	175	$^{\circ}$	
T _{stg}	Storage Temperature	-55~175	$^{\circ}$	

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth(j-c)	Channel-to-case thermal resistance	0.75	°C/W





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ELECTRICAL CHARACTERISTICS

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D =250 μ A	55			V
V _{GS(th)}	Gate Threshold Voltage	VDS=VGS; I _D =250 μ A	2.0		4.0	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =59A			8	mΩ
lgss	Gate-Source Leakage Current	V _{GS} = ±20V			±0.1	μА
I _{DSS}	Drain-Source Leakage Current	V _{DS} =55V; V _{GS} = 0V			25	μА
V _{SD}	Diode forward voltage	I _S =59A, V _{GS} = 0V			1.3	V

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